

### AMENDMENTS TO THE CLAIMS

Claims 1-67 were pending prior to the entry of these amendments. Please amend Claims 5, 6, 9, 16, 17, 20, 45, 46, 49, and 55-57 as indicated below. Please cancel Claims 1-4, 8, 12-15, 19, 24-44, 48, and 58-61 without prejudice as indicated below. Please add new Claims 68-70 as indicated below.

1. (Canceled)

2. (Canceled)

3. (Canceled)

4. (Canceled)

5. (Currently Amended) The apparatus of claim 9 [[3]], wherein the top surface is adapted to polish the surface.

6. (Currently Amended) The apparatus of claim 2 [[2]] further comprising a mechanism configured to establish relative motion between the surface and the pad.

7. (Original) The apparatus of claim 6, wherein the top surface is adapted to touch the surface for polishing.

8. (Canceled)

9. (Currently Amended) The apparatus of claim 8 An apparatus for removing a conductive material from a surface of a wafer, using a solution, comprising:

at least one electrical contact configured to be placed in proximity of the surface and adapted to electrically connect the at least one electrical contact with the surface without physically touching the surface, wherein the electrical contact and the surface are electrically connected through the solution;

an electrode configured to be in the presence of the solution wherein upon application of a potential difference between the at least one electrical contact and the electrode the conductive material is removed from the surface; and

a pad having a top surface positioned between the surface and the electrode, wherein the at least one contact is in the pad, wherein the at least one contact includes a conductive element, wherein the pad rests on the conductive element and the pad includes at least one opening to receive the at least one contact.

10. (Original) The apparatus of claim 9, wherein the conductive element includes a bias mechanism to urge the pad against the surface of the wafer.

11. (Original) The apparatus of claim 10 further comprising a wafer holder to retain the wafer and place the surface against the top surface of the pad.

12. (Cancelled)

13. (Cancelled)

14. (Cancelled)

15. (Cancelled)

16. (Currently Amended) The apparatus of claim 20 [[14]], wherein the top surface is adapted to polish the surface of the wafer.

17. (Currently Amended) The apparatus of claim 20 [[14]] further comprising a mechanism to establish relative motion between the surface and the pad.

18. (Original) The apparatus of claim 17, wherein the top surface is adapted to touch the surface.

19. (Cancelled)

20. (Currently Amended) The apparatus of claim 19 An apparatus for removing a conductive material from a surface of a wafer, using a solution, comprising:

at least one electrical contact configured to be placed in proximity of the surface and adapted to electrically connect the at least one electrical contact with the surface without physically touching the surface, wherein the electrical contact and the surface are electrically connected through the solution;

an electrode configured to be in the presence of the solution wherein upon application of a potential difference between the at least one electrical contact and the electrode the conductive material is removed from the surface; and

a pad having a top surface positioned between the surface and the electrode, wherein the at least one contact includes a plurality of contacts, wherein the plurality of contacts includes a conductive element connecting the plurality of contacts, wherein the pad rests on the conductive element and the pad includes a plurality of openings to receive the plurality of contacts.

Appl. No. : 10/826,219  
Filed : April 16, 2004

21. (Original) The apparatus of claim 20, wherein the plurality of contacts is distributed in a pattern.

22. (Original) The apparatus of claim 21, wherein the conductive element is biased towards the surface of the wafer to push the pad against the surface as the top surface of the pad touches the surface.

23. (Original) The apparatus of claim 22 further comprising a wafer holder to retain the wafer and adjust a distance between the top surface of the pad and the surface of the wafer.

24. (Canceled)

25. (Canceled)

26. (Canceled)

27. (Canceled)

28. (Canceled)

29. (Canceled)

30. (Canceled)

31. (Canceled)

32. (Canceled)

33. (Canceled)

34. (Canceled)

35. (Canceled)

36. (Canceled)

37. (Canceled)

38. (Canceled)

39. (Canceled)

40. (Canceled)

41. (Canceled)

42. (Canceled)

43. (Canceled)

44. (Canceled)

45. (Currently Amended) The apparatus of claim 49 [[43]], wherein the top surface is adapted to polish the surface of the wafer.

46. (Currently Amended) The apparatus of claim 49 [[43]] further comprising a mechanism configured to establish relative motion between the surface and the pad.

47. (Original) The apparatus of claim 46, wherein the top surface of the pad touches the front surface of the wafer to assist in removing the conductive material.

48. (Canceled)

49. (Currently Amended) The apparatus of claim 48 An apparatus to electropolish a conductive material off a front surface of a wafer, using a solution and a power source, comprising:

a plurality of electrical contacts positioned in proximity of the front surface without touching the surface;

an electrode configured to be connected to the power source so that when a potential is applied between the plurality of electrical contacts and the electrode, an electrical current passes through the solution to electropolish the conductive material off the front surface; and

a pad having a top surface positioned between the surface and the electrode wherein the solution flows between the top surface of the pad and the surface of the wafer, wherein the plurality of contacts includes a conductive element connecting the plurality of contacts, wherein the pad includes a plurality of openings configured to receive the plurality of contacts.

50. (Original) The apparatus of claim 49, wherein the plurality of contacts is distributed in a pattern.

51. (Original) The apparatus of claim 50, wherein the conductive element includes a bias mechanism to urge the pad against the surface of the wafer.

52. (Original) The apparatus of claim 51 further comprising a wafer holder to retain the wafer and adjust a distance between the top surface of the pad and the surface of the wafer.

53. (Original) The apparatus of claim 49, wherein the pad includes channels for solution flow.

54. (Original) The apparatus of claim 49, wherein the pad is porous.

55. (Currently Amended) The apparatus of claim 49 [[43]], wherein the top surface of the pad includes abrasives.

56. (Currently Amended) The apparatus of claim 49 [[43]], wherein the pad includes channels for solution flow.

57. (Currently Amended) The apparatus of claim 49 [[43]], wherein the pad is porous.

58. (Canceled)

59. (Canceled)

60. (Canceled)

61. (Canceled)

62. (Original) A liquid contact electropolishing apparatus to polish a conductive surface using a solution, comprising:

a cathode having a plurality of cathode openings and configured to contact the solution; and

a pad having a top surface disposed over the cathode, the pad having a plurality of pad openings which corresponds to the plurality of cathode openings; and

an anode having a plurality of raised tips configured in the plurality of openings and immersed in the solution wherein an electrical connection between the anode, cathode, and the conductive surface occurs through the solution to remove the conductive surface.

63. (Original) The liquid contact electropolishing apparatus of claim 62 further comprising a pad having a top surface configured to contact the conductive surface.

64. (Original) The liquid contact electropolishing apparatus of claim 63, wherein the top surface is adapted to polish the conductive surface.

65. (Original) The liquid contact electropolishing apparatus of claim 64 further comprising a mechanism to establish relative motion between the conductive surface and the top surface of the pad to planarize the conductive surface.

66. (Original) The liquid contact electropolishing apparatus of claim 62, wherein: the raised tips of the anode are electrically isolated from cathode; and the pad openings are larger than the cathode openings.

Appl. No. : 10/826,219  
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67. (Original) The liquid contact electropolishing apparatus of claim 66, wherein the plurality of openings of the pad defines a plurality of material removal areas and the relative motion provides conductive material removal throughout the conductive surface.

68. (New) The apparatus of claim 10, wherein the bias mechanism comprises at least one spring disposed on a side of the conductive element opposite to the pad.

69. (New) The apparatus of claim 22, wherein the conductive element is biased by at least one spring disposed on a side of the conductive element opposite to the pad.

70. (New) The apparatus of claim 51, wherein the bias mechanism comprises at least one spring disposed on a side of the conductive element opposite to the pad.